2025-02-14(금), 15:10-17:10
좌장: 추후업데이트 예정

E. Compound Semiconductors 분과

[FN3-E] WBG Semiconductor-I

초청 FN3-E-1 15:10-15:40	**MOCVD-based AlGaN/GaN HEMT Epitaxy Technology for RF and Power Semiconductors** Young-Hun Han[1], June-O Song[1], Ji-Hyung Moon[1], Hyung Sun Yun[1], Tae-Kyung Kim[1], Byoung-Cgul Jun[2], Jae-Hak Lee[3], and Dae-Hyun Kim [1]WaveLord. Inc, [2]Wavice. Inc, [3]School of Electronic and Electrical Engineering, Kyungpook National University
FN3-E-2 15:40-15:55	**Improved f_{max} in Short-L_g $Al_{0.4}Ga_{0.6}N$/GaN HEMTs with $Al_{0.08}Ga_{0.92}N$ Back-barrier** Wan-Soo Park[1], Hyeok-Jun Lee[1], Su-Min Choi[1], Sang-Kuk Kim[2], Jae-Hak Lee[1], Tae-Woo Kim[3], Kyounghoon Yang[4], and Dae-Hyun Kim [1]Kyungpook National University,[2]QSI,[3]Texas Tech University, [4]KAIST
FN3-E-3 15:55-16:10	**Impact of Gate Field Plate on Kink Phenomenon in S22 of AlGaN/GaN HEMTs for RF Applications: A Comparative Study** Xuejing Yang[1], Yongsik Jeong[1], Wan-Soo Park[2], Su-Min Choi[2], Dae-Hyun Kim[2], and Kyounghoon Yang[1] [1]KAIST, [2]Kyungpook National University
FN3-E-4 16:10-16:25	**Positive-Bias-Stress Instability (PBTI) and Fast Trap Generation in AlGaN/GaN HEMTs during On-State Condition** Kevin Samways and Tae-Woo Kim Department of Electrical and Computer Engineering, TTU, Texas
FN3-E-5 16:25-16:40	**Lg = 50 nm $In_{0.17}Al_{0.83}N$/GaN HEMTs with f_T = 120 GHz and f_{max} = 300 GHz** Hyeok-Jun Lee[1], Su-Min Choi[1], Wan-Soo Park[1], Hyo-Jin Kim[1], Jae-Hak Lee[1], Kyounghoon Yang[2], and Dae-Hyun Kim[1] [1]School of Electronic and Electrical Engineering, Kyungpook National University, [2]KAIST
FN3-E-6 16:40-16:55	**Device-Level Thermal Management of GaN HEMTs Through Electro-Thermal Modeling** Changhwan Song, Jisu Kim, and Jungwan Cho School of Mechanical Engineering, Sungkyunkwan University

FN3-E-7 16:55-17:10	Evaluation of Al-rich AlGaN Channel Layers in HEMTs Grown by Conventional and Pulsed Flow MOCVD Techniques Shyam Mohan, Joocheol Jeong, Jooyong Park, Joonhyuk Lee, Jaejin Heo, and Okhyun Nam CANS, Department of Nano Semiconductor, Tech University of Korea